

depositing a second conductive layer over said first conductive layer.

18. (Amended) The method in claim 17, wherein said step of exposing said first conductive layer to a nitrogen free passivation gas further comprises exposing said first conductive layer to a nitrogen free passivation gas *ex situ*.

19. (Amended) A method of forming a capacitor, comprising:  
forming a capacitor plate, comprising:

providing a first conductive layer in a first environment;

exposing said first conductive layer to a passivation gas; wherein said step of exposing said first conductive layer to a passivation gas further comprises exposing said first conductive layer to silane in a second environment; and

depositing a second conductive layer over said first conductive layer.

20. (Amended) The method in claim 17, wherein said step of exposing said first conductive layer comprises exposing said first conductive layer to a nitrogen free passivation gas *in situ*.

21. (Amended) The method in claim 17, wherein said step of exposing said first conductive layer comprises exposing said first conductive layer to a nitrogen free passivation gas while still in said first environment.

22. (Amended) The method in claim 17, wherein said step of providing a first conductive layer comprises providing a first conductive layer in an oxygen-free environment; and wherein said step of exposing said first conductive layer comprises exposing said first conductive layer to a nitrogen free passivation gas in said oxygen-free environment.

B2 34. (Amended) The method in claim 22, wherein said step of depositing a second conductive layer comprises depositing said second conductive layer in a second nitrogen free-environment.

Please add new claims 76-81 as follows:

B3 cont.  
76. (New) A method of forming a capacitor, comprising:  
forming a capacitor plate, comprising:  
providing a first conductive layer in a first environment;  
exposing the first conductive layer to a plasma in a second environment; and  
depositing a second conductive layer over the first conductive layer.

77. (New) The method of claim 76 wherein the plasma comprises a selection of  $N_2/H_2$ ,  $N_2$ , and  $NH_3$  plasmas.

78. (New) The method of claim 76 wherein the first conductive layer is not exposed to oxygen between being provided in the first environment and being exposed to the plasma in the second environment.

79. (New) A method of forming a capacitor, comprising:  
forming a capacitor plate, comprising:  
providing a first conductive layer in a first environment;  
exposing the first conductive layer to a selection of  $B_2H_6$ ,  $PH_3$ ,  $CH_3SiH_3$ ,  $(CH_3)_3Si-Si(CH_3)_3$ , HMDS,  $CF_4$ ,  $CHF_3$ ,  $HCL$ ,  $BCl_3$ , and  $SiH_4$  gases, and combinations thereof, in a second environment; and  
depositing a second conductive layer over the first conductive layer.

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